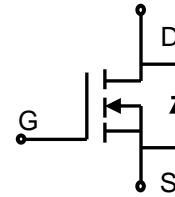




Applications

- ◆ Motor Drives
- ◆ UPS
- ◆ DC-DC Converter
- ◆ Energy Storage



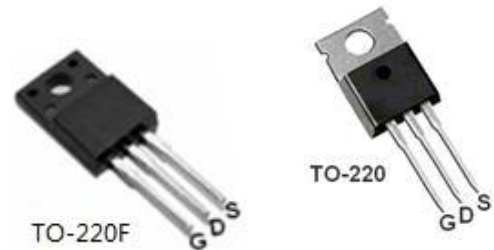
N-Channel MOSFET

Features

- ◆ 85V,180A, $R_{DS(on),max}=2.55m\Omega@V_{GS} = 10V$
- ◆ Improved dv/dt capability
- ◆ Fast switching
- ◆ 100% EAS Guaranteed
- ◆ Green device available

Product Summary

V_{DSS}	85V
$R_{DS(on),max}@V_{GS}=10V$	2.55m Ω
I_D	180A



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	85	V
Continuous drain current ($T_C = 25^\circ\text{C}$,Silicon limit)	I_D	303	A
($T_C = 25^\circ\text{C}$, Package limit)		180	A
($T_C = 100^\circ\text{C}$,Silicon limit)		192	A
Pulsed drain current ¹⁾	I_{DM}	720	A
Gate-Source voltage	V_{GSS}	± 20	V
Avalanche energy ²⁾	E_{AS}	1568	mJ
Power Dissipation	P_D	391	W
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.32	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient ³⁾	$R_{\theta JA}$	49.14	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube
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Electrical Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0\text{ V}, I_D=250\mu\text{A}$	85	---	---	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.5	---	4.5	V
Drain-source leakage current	I_{DSS}	$V_{DS}=85\text{ V}, V_{GS}=0\text{ V}, T_J = 25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=85\text{ V}, V_{GS}=0\text{ V}, T_J = 150^\circ\text{C}$	---	---	10	mA
Gate leakage current, Forward	I_{GSSF}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	---	---	100	nA
Gate leakage current, Reverse	I_{GSSR}	$V_{GS}=-20\text{ V}, V_{DS}=0\text{ V}$	---	---	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=50\text{ A},$ $T_J = 25^\circ\text{C}$	---	2.15	2.55	m Ω
		$T_J = 150^\circ\text{C}$	---	3.6	---	
Forward transconductance	g_{fs}	$V_{DS}=5\text{ V}, I_D=100\text{ A}$	---	138	---	S
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{DS} = 42.5\text{ V}, V_{GS} = 0\text{ V},$ $f = 250\text{ kHz}$	---	8276	---	pF
Output capacitance	C_{oss}		---	1852	---	
Reverse transfer capacitance	C_{rss}		---	30.6	---	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 42.5\text{ V}, V_{GS}=10\text{ V}, I_D = 50\text{ A}$	---	131	---	ns
Rise time	t_r		---	199	---	
Turn-off delay time	$t_{d(off)}$		---	182	---	
Fall time	t_f		---	101	---	
Gate resistance	R_g	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}, f=1\text{ MHz}$	---	1.4	---	Ω
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DS}=68\text{ V}, I_D=50\text{ A},$ $V_{GS}= 10\text{ V}$	---	63.6	---	nC
Gate to drain charge	Q_{gd}		---	57	---	
Gate charge total	Q_g		---	211	---	
Gate plateau voltage	$V_{plateau}$		---	5.1	---	V
Output Charge	Q_{oss}	$V_{DS}=68\text{ V}, V_{GS}= 0\text{ V}$	---	246	---	nC
Drain-Source diode characteristics and Maximum Ratings						
Continuous Source Current	I_S		---	---	180	A
Pulsed Source Current	I_{SM}		---	---	720	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{ V}, I_S=50\text{ A}, T_J=25^\circ\text{C}$	---	---	1.1	V
Reverse Recovery Time	t_{rr}	$I_S=50\text{ A}, di/dt=100\text{ A}/\mu\text{s}, T_J=25^\circ\text{C}$	---	57.3	---	ns
Reverse Recovery Charge	Q_{rr}		---	75.2	---	nC

Notes:

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2: $V_{DD}=80\text{ V}, V_{GS}=10\text{ V}, L=1\text{ mH}, I_{AS}=56\text{ A}, R_G=25\Omega,$ Starting $T_J=25^\circ\text{C}.$
- 3: The value of R_{thJA} is measured by placing the device in a still air box which is one cubic foot.



Figure 1. Typ. Output Characteristics

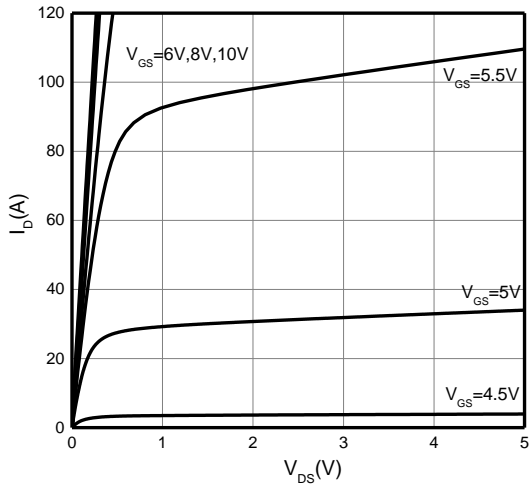


Figure 2. Transfer Characteristics

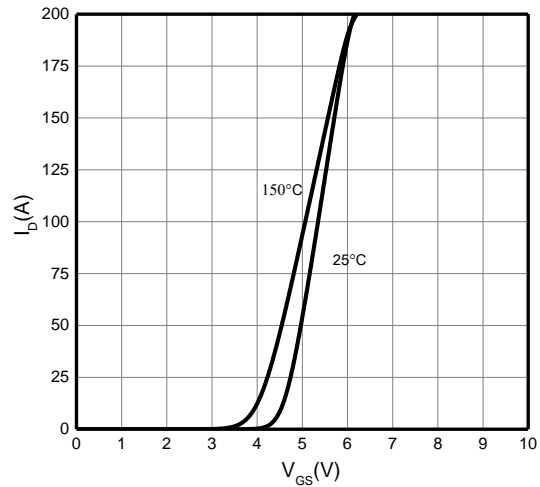


Figure 3. On-Resistance vs. Drain Current

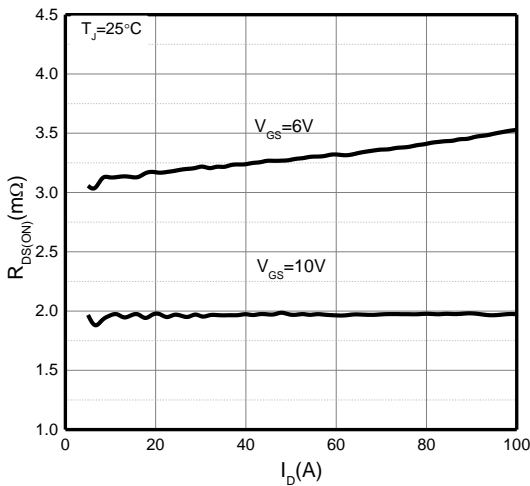


Figure 4. On-Resistance vs. Temperature

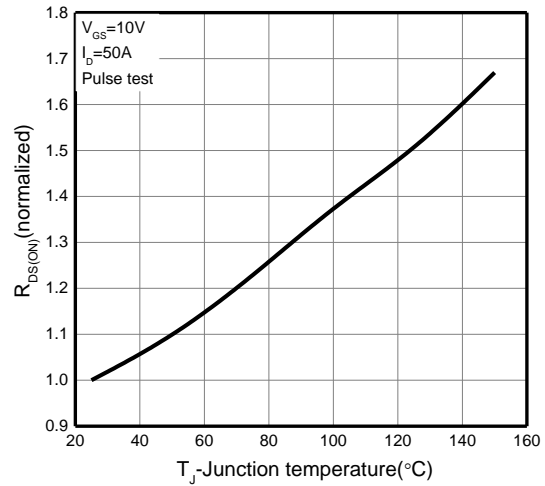


Figure 5. Breakdown Voltage vs. Temperature

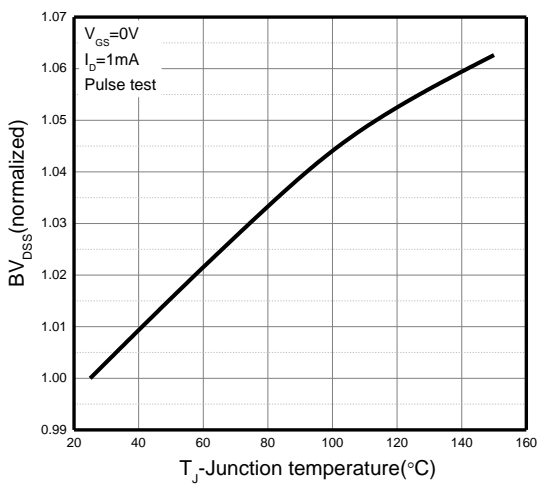


Figure 6. Threshold Voltage vs. Temperature

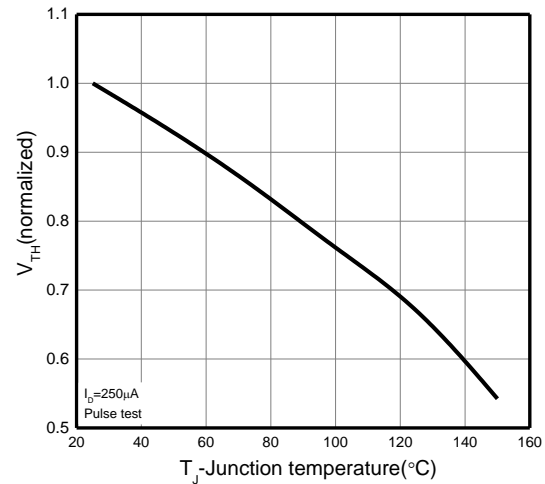




Figure 7. $R_{DS(on)}$ vs. Gate Voltage

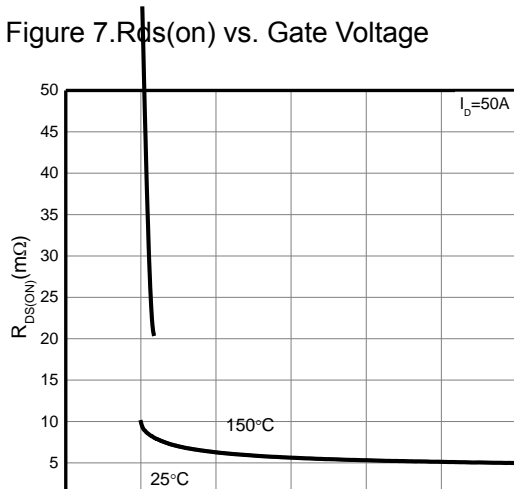


Figure 8. Body-Diode Characteristics

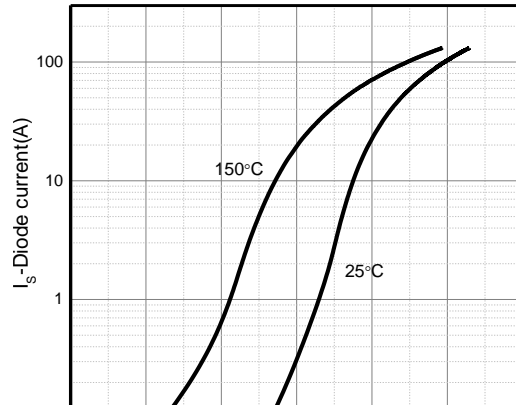


Figure 9. Capacitance Characteristics

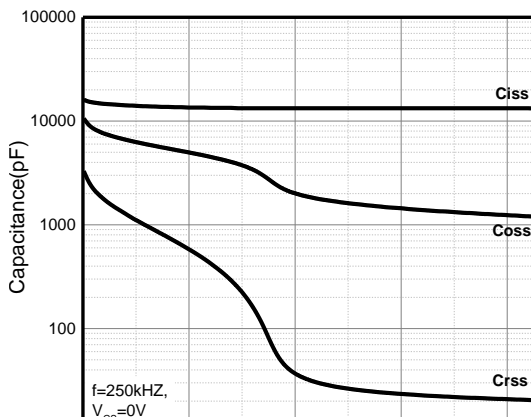


Figure 10. Gate Charge Characteristics

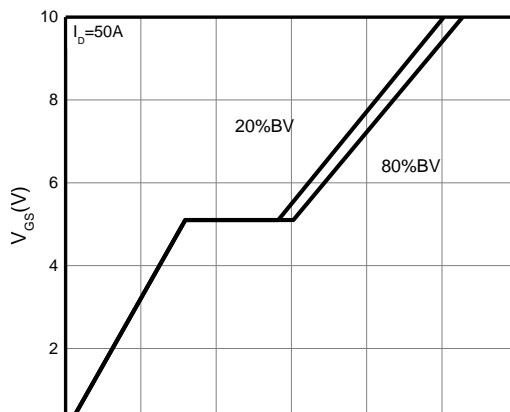


Figure 11. Drain Current Derating

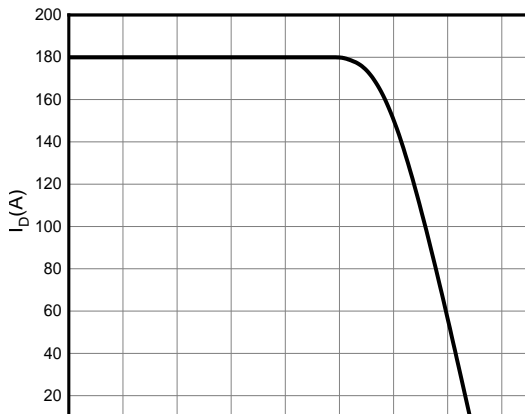


Figure 12. Power Dissipation vs. Temperature





Figure 13. Safe Operating Area

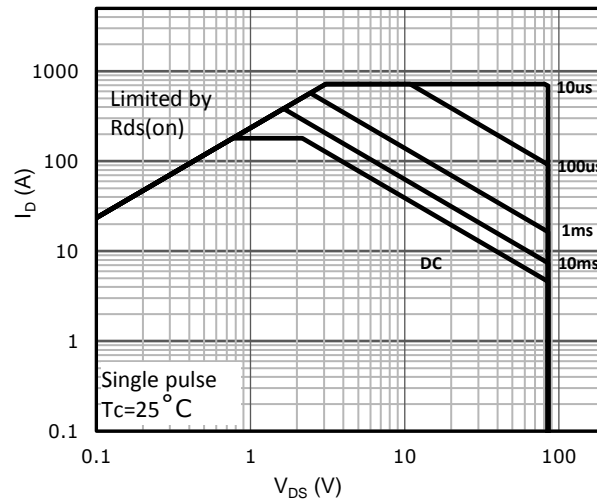
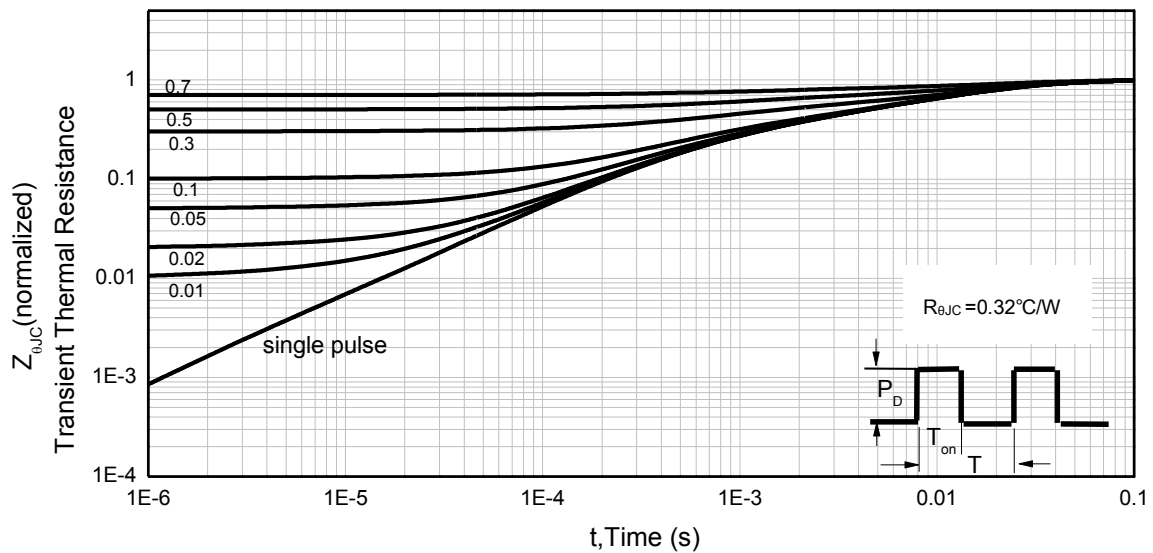
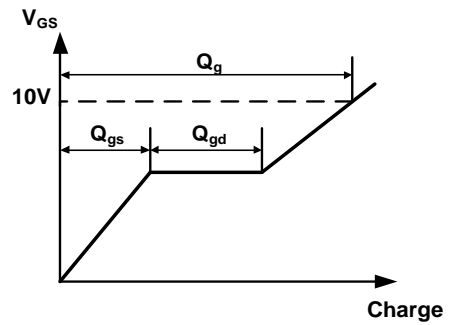
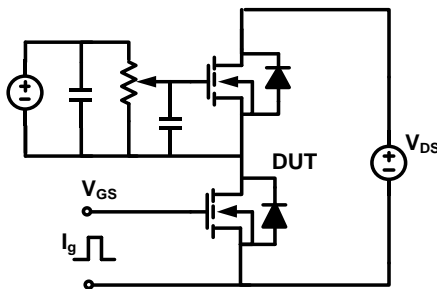


Figure 14. Normalized Maximum Transient Thermal Impedance (RthJC)

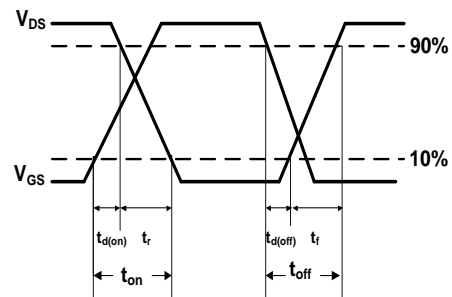
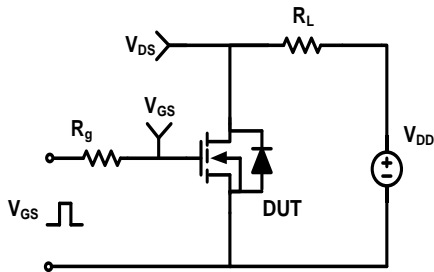




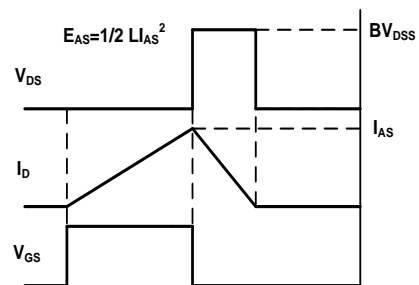
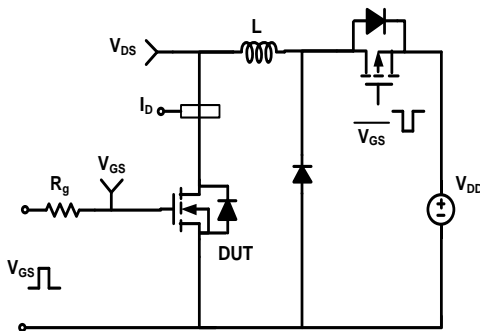
Gate Charge Test Circuit & Waveform



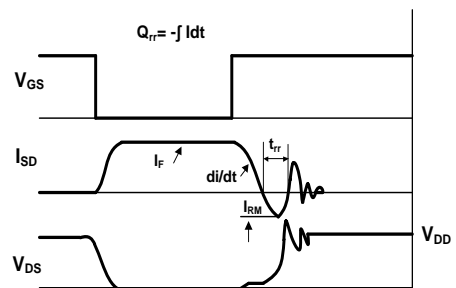
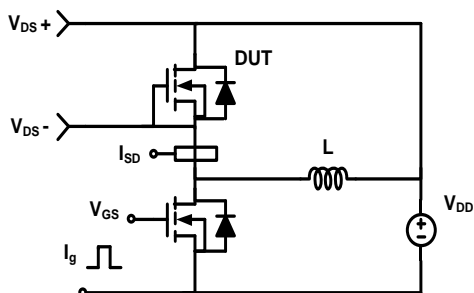
Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveform



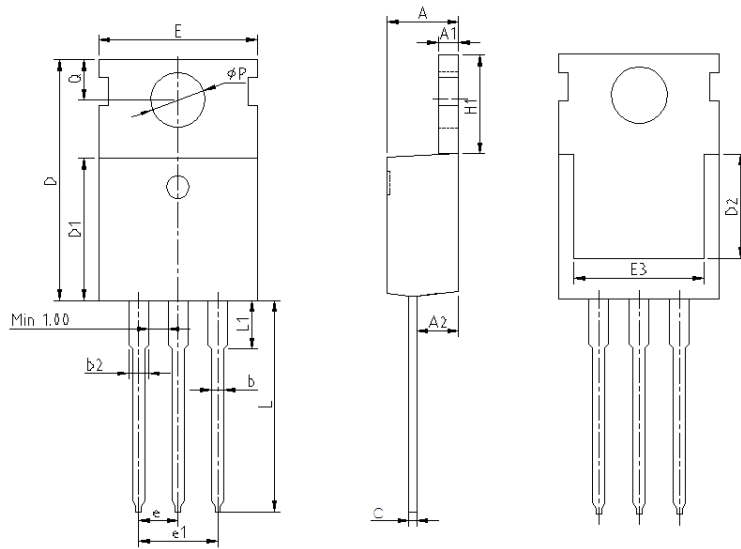
Diode Recovery Test Circuit & Waveform





WLP025N85

N-Ch 85V Fast Switching MOSFETs



DIMENSIONS IN MILLITMETERS		
SYMBOL	MIN	MAX
A	4.25	4.7
A1	1.2	1.4
A2	2.2	2.92
b	0.7	0.97
b2	1.14	1.78
c	0.4	0.61
D	14.32	16.1
D1	8.39	9.4
D2	5.5	7
E	9.7	10.36
E3	7	8.78
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	14.4
L1	-	4.05
ΦP	3.4	3.8
Q	2.54	3